

#### **Features**

- High Density Cell Desihn for Ultra Low R<sub>DS(on)</sub>
- · Fully Characterized Avalanche Voltage and Current
- Good Stability and Uniformity with High EAS
- · Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

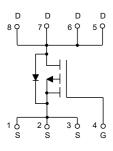
- Operating Junction Temperature Range: -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 1.15°C/W Junction to Case<sup>(Note 2)</sup>

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V <sub>DS</sub>	-60	V
Gate-Source Volltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C	1	-60	Α
	T <sub>C</sub> =100°C	- I <sub>D</sub>	-42.3	Α
Pulsed Drain Current		I <sub>DM</sub>	-260	Α
Single Pulse Avalanche Energy (Note 3)		E <sub>AS</sub>	722	mJ
Total Power Dissipation		P <sub>D</sub>	130	W

#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. Surface Mounted on FR4 Board, t≤10 sec.
- 3.  $T_J$ =25°C, $V_{DD}$ =-30V, $V_G$ =-10V,L=0.5mH, $R_Q$ =25 $\Omega$ .

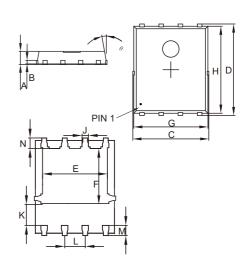
# **Internal Structure and Marking Code**





# P-CHANNEL MOSFET

# **DFN5060**



DIMENSIONS						
DIM	M INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOIL	
Α	0.031	0.047	0.80	1.20		
В	0.010		0.254		TYP.	
С	0.193	0.222	4.90	5.64		
D	0.232	0.250	5.90	6.35		
E	0.148	0.167	3.75	4.25		
F	0.126	0.154	3.20	3.92		
G	0.189	0.213	4.80	5.40		
Н	0.222	0.239	5.65	6.06		
K	0.045	0.059	1.15	1.50		
J	0.012	0.020	0.30	0.50		
L	0.046	0.054	1.17	1.37		
М	0.012	0.028	0.30	0.71		
N	0.016	0.028	0.40	0.71		



# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

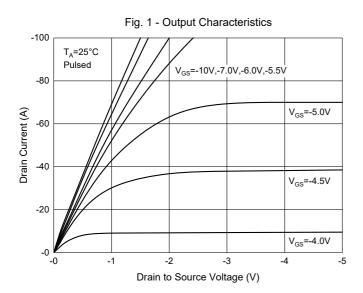
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250µA	-60			V
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA
Gate-Threshold Voltage <sup>(Note 4)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-2	-2.6	-3.5	V
Drain-Source On-Resistance(Note 4)	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A		13	18	mΩ
Forward Tranconductance(Note 4)	<b>9</b> FS	V <sub>DS</sub> =-5V, I <sub>D</sub> =-20A		25		S
Dynamic Characteristics(Note 5)						
Input Capacitance	C <sub>iss</sub>			5814		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-25V,V <sub>GS</sub> =0V,f=1MHz		483		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			234		
Total Gate Charge	Qg			75		nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =-30V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-20A		16		
Gate-Drain Charge	$Q_{gd}$			19		
Reverse Recovery Chrage	Q <sub>rr</sub>	I <sub>s</sub> =-20A, di/dt=-100A/µs		71		
Reverse Recovery Time	t <sub>rr</sub>	1520A, di/di100A/µ5		49		
Turn-On Delay Time	t <sub>d(on)</sub>			18		
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}$ =-30V, $R_{L}$ =1.5 $\Omega$ ,		20		ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{G}$ =3 $\Omega$		55		
Turn-Off Fall Time	t <sub>f</sub>			35		
Drain-Source Body Diode Cha	racteristi	cs	•	•		
Continuous Body Diode Current	Is	T <sub>C</sub> =25°C			-60	Α
Body Diode Voltage	V <sub>SD</sub>	I <sub>SD</sub> =-20A, V <sub>GS</sub> =0V			-1.2	V

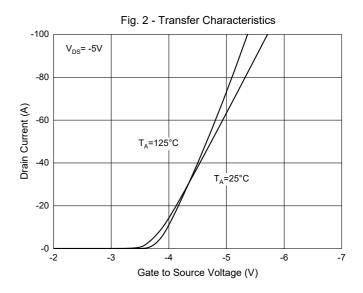
Note 4. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤2%.

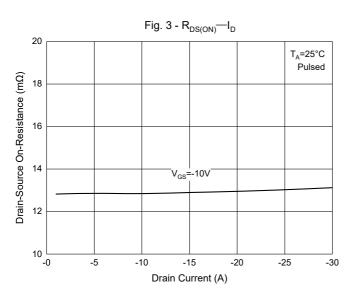
<sup>5.</sup> Guaranteed by Design, Not Subject to Production Testing.

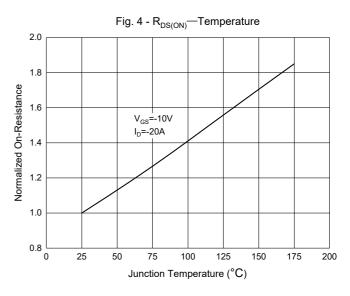


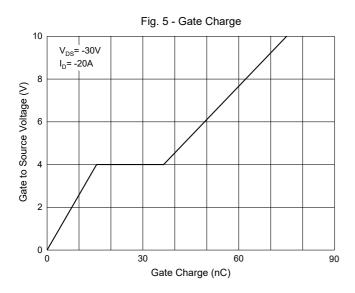
### **Curve Characteristics**













# **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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